

## 1. Benefits

- Higher safety margin against overvoltage
- Improved efficiency all load conditions
- Increased efficiency compared to Silicon Diode alternatives
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

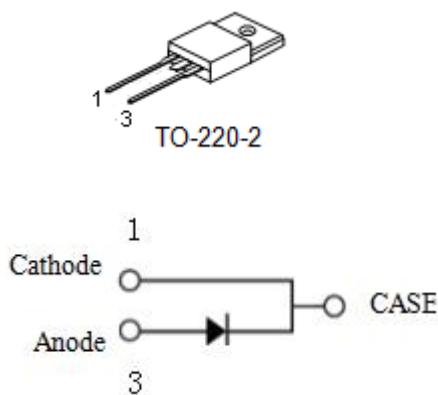
## 2. Features

- 650-Volt Schottky Rectifier
- Shorter recovery time
- High-speed switching possible
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on VF

## 3. Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives
- HID Lighting

## 4. Pin configuration



Pin	Function
1	Cathode
2	-
3	Anode

## 5. Absolute Maximum Ratings

( $T_J=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Rating	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	650	V
Surge Peak Reverse voltage	$V_{RSM}$	650	V
DC Blocking Voltage	$V_{DC}$	650	V
Continuous forward current $T_C = 25^\circ\text{C}$ $T_C = 135^\circ\text{C}$ $T_C = 150^\circ\text{C}$	$I_F$	30 14 10	A
Repetitive Peak Forward Current	$I_{FRM}$	70	A
Surge no repetitive forward current	$I_{FSM}$	90	A
Power Dissipation $T_C = 25^\circ\text{C}$ $T_C = 135^\circ\text{C}$	$P_D$	136 59	W
Operating Junction and storage temperature	$T_J, T_{stg}$	-55 to +175	°C

## 6. Thermal characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Thermal resistance	$R_{th(j-c)}$	-	-	2.6	-	°C/W

## 7. Electrical characteristics

Parameter	Symbol	Conditions	Rating			Unit	
			Min	Typ	Max		
Gate Threshold Voltage	$V_F$	$I_F=10\text{A}$	$T_C=25^\circ\text{C}$	-	1.4	1.8	V
			$T_C=175^\circ\text{C}$	-	2.1	3	
Reverse Current	$I_R$	$V_R=650\text{V}$	$T_C=25^\circ\text{C}$	-	13	100	$\mu\text{A}$
			$T_C=175^\circ\text{C}$	-	48	400	
Total Capacitive Charge	$Q_C$	$VR = 400\text{V}, IF = 10\text{A}$ $T_J = 25^\circ\text{C}$ $Q_C = \int_0^{VR} C(V) dv$	-	30	-	nC	
Total Capacitance	$C$	$T_J = 25^\circ\text{C}, f = 1\text{MHz}$	$V_R=0\text{V}$	-	485	$\text{pF}$	
			$V_R=200\text{V}$		60		
			$V_R=400\text{V}$		42		
Capacitance Stored Energy	$EC$	$VR=400\text{V}$	-	5.1	-	$\mu\text{J}$	

## 8. Typical Characteristics

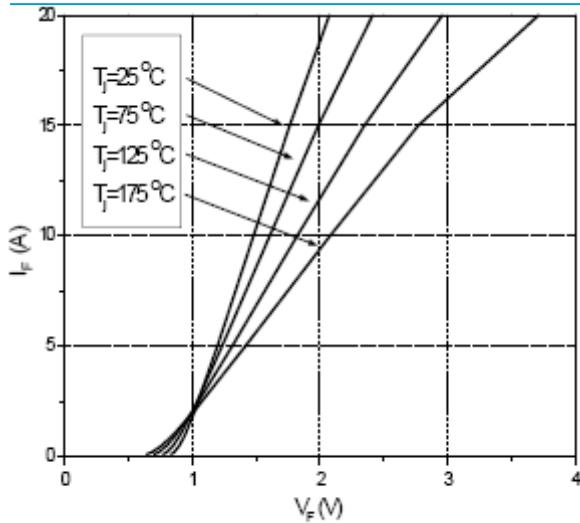


Figure 1. Forward Characteristics

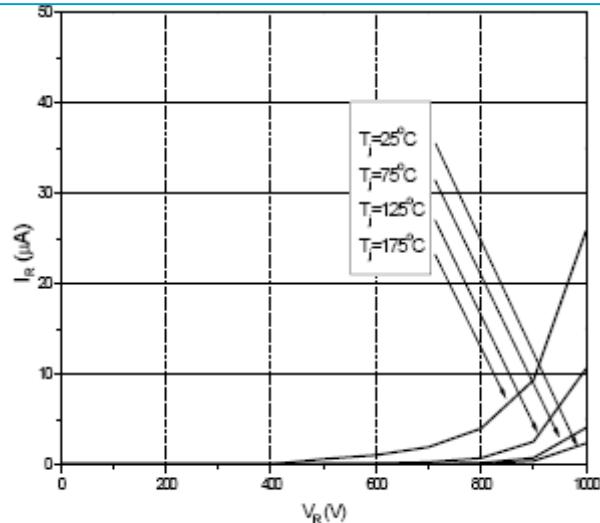


Figure 2. Reverse Characteristics

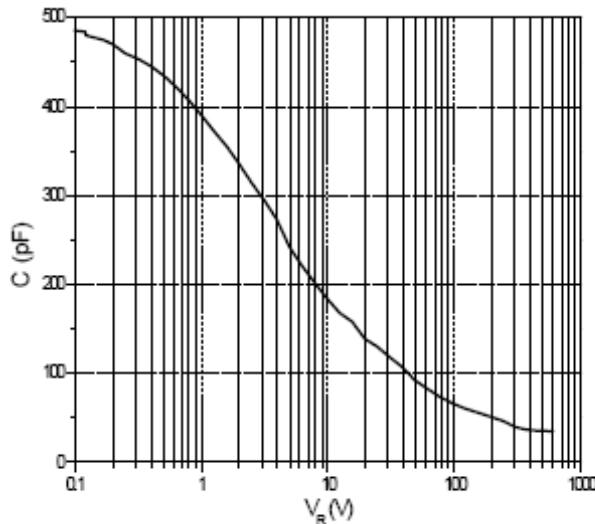


Figure 3. Capacitance vs. Reverse Voltage

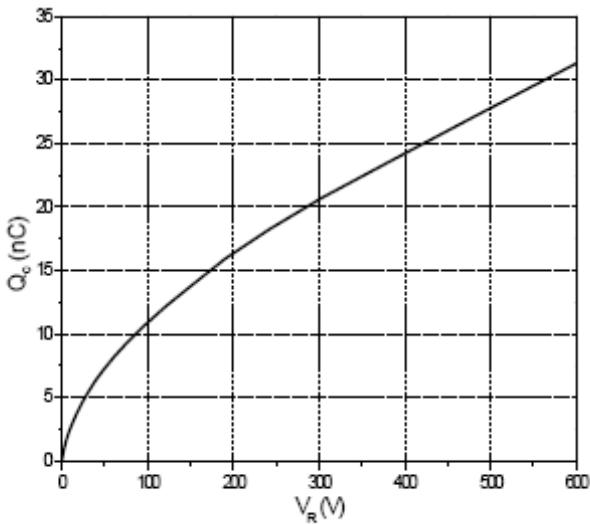


Figure 4. Total Capacitance Charge vs. Reverse Voltage

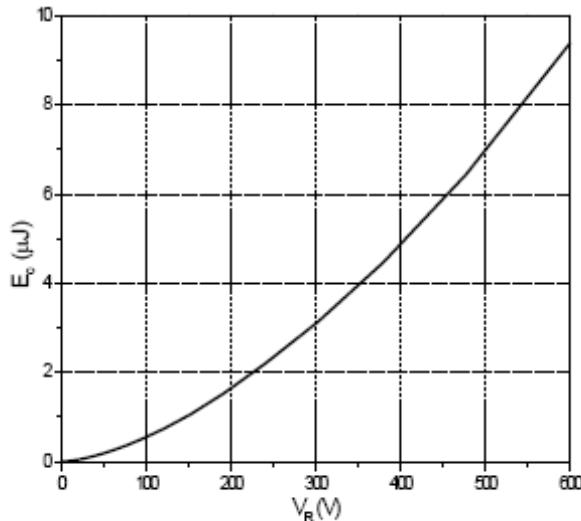


Figure 5. Capacitance Stored Energy

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